**Product Specification** 

1003.309001

Part Number	Customer				
<b>Category</b> OverallWafer	Parameter		Specification	Measurement Method	
	1.0	Diameter	150.00 +/- 0.50 mm	WaferVendor	
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor	
	3.0	Primary Flat Orientation	{110}+/- 1.0 degree	Wafer Vendor	
	4.0	Growth Method	CZ	Wafer Vendor	
	5.0	Туре	Any	Wafer Vendor	
	6.0	Dopant	any	Wafer Vendor	
	7.0	Resistivity	1 - 100 ohm cm	Wafer Vendor	
	8.0	Overall Thickness	400.00 +/- 5.00 um	Wafer Vendor	
	9.0	Total Thickness Variation (TTV)	<5.00um	Guaranteed by process	
	10.0	Bow	<50.00um	ADE measurement	
	11.0	Warp	<50.00um	ADE measurement	
	12.0	Orientation	<100>+/-1.0	Wafer Vendor	
	13.0	Back Surface Quality	Polished with laser mark	Wafer Vendor	
	14.0	Front Surface Quality	Prime	Wafer Vendor	
	15.0	Edge Chips	None	Bright Light 100% (note 2)	
HandleSilicon	16.0	Handle Thickness	400.00 +/- 5.00 um	100% ADE measurement	
DeviceSilicon	17.0	Haze	None	Bright Light, 100% (note 2).	
	18.0	Scratches	None	Bright Light, 100% (note 2).	

Icemos Technology Ltd

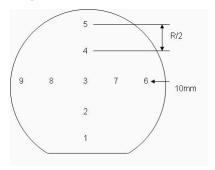
**Product Specification** 

1003.309001

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information